NSR0320MW2T1

Schottky Barrier Diodes

These Schottky barrier diodes are designed for high current, handling capability, and low forward voltage performance.

Features

- Low Forward Voltage 0.24 Volts (Typ) @ $I_F = 10 \text{ mAdc}$
- High Current Capability
- ESD Rating Human Body Model: CLASS 3B – Machine Model: C
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = $125^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	20	Vdc
Peak Revese Voltage	V _{RM}	23	V
Forward Power Dissipation @ T _A = 25°C Derate above 25°C	P _F	200 2.0	mW mW/°C
Forward Current (DC) Continuous	١ _F	1	A
Forward Current t = 8.3 ms Half Sinewave	١ _F	5	A
Junction Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

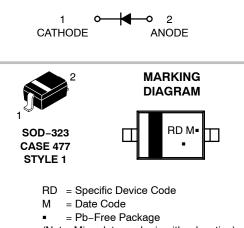
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com

HIGH CURRENT SCHOTTKY BARRIER DIODE



(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NSR0320MW2T1G	SOD-323 (Pb-Free)	· ·
NSR0320MW2T3G	SOD-323 (Pb-Free)	10,000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Semiconductor Components Industries, LLC, 2010 September, 2010 – Rev. 3

NSR0320MW2T1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Мах	Unit
Total Capacitance (V _R = 5.0 V, f = 1.0 MHz)	CT	-	25	29	pF
Reverse Leakage (V _R = 15 V)	I _R	-	10	50	μΑ
Reverse Leakage (V _R = 2.0 V @ 85°C)	۱ _R	-	200	300	μΑ
Reverse Leakage (V _R = 15.0 V @ 85°C)	I _R	-	450	1000	μA
Forward Voltage (I _F = 10 mA)	V _F	-	0.24	0.27	V
Forward Voltage (I _F = 100 mA)	V _F	-	0.30	0.35	V
Forward Voltage (I _F = 900 mA)	V _F	-	0.45	0.50	V

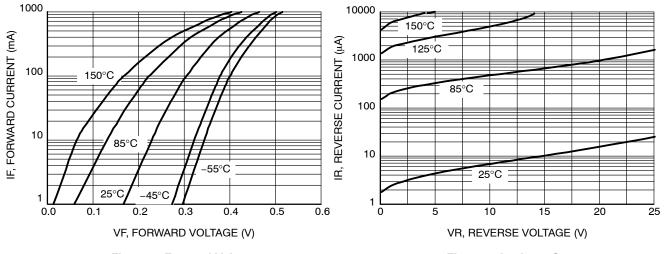




Figure 2. Leakage Current

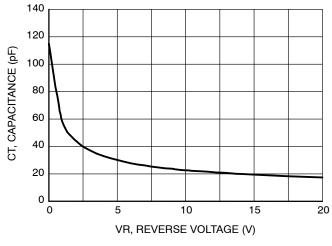


Figure 3. Total Capacitance

PACKAGE DIMENSIONS

SOD-323 CASE 477-02 **ISSUE H**

NOTES:

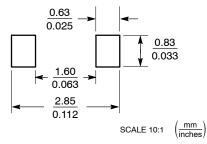
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982
 - CONTROLLING DIMENSION: MILLIMETERS.
- З. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
- 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. 5. DIMENSION L IS MEASURED FROM END OF

RADIUS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
С	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
HE	2.30	2.50	2.70	0.090	0.098	0.105

STYLE 1: PIN 1. CATHODE 2. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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